

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

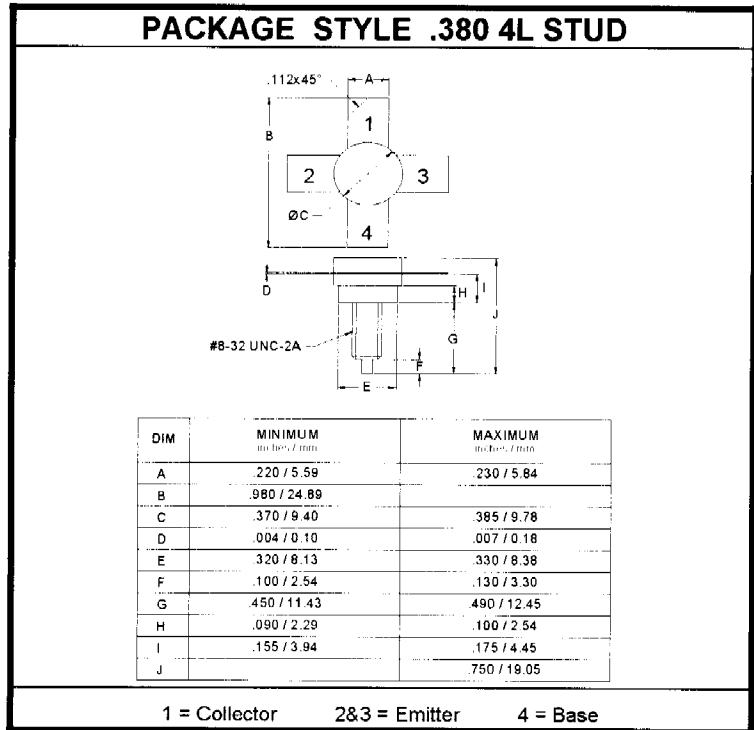
BLY92C is designed for Class C FM amplifier applications up to 250 MHz.

FEATURES:

- $P_G = 11$ dB typical at 175 MHz
- High VSWR capability
- **Omnigold™** Metalization System

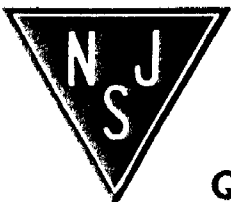
MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	40 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.4 °C/W



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	10		100	---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz		40	50	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 15$ W $f = 175$ MHz	10	11		dB
η_c	$P_{IN} = 1.0$ W	50	60		%



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